

IV. AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A processing apparatus for processing a substrate on a surface of which a film is formed, comprising:

a film removing member for selectively removing the film on a predetermined portion of an outer peripheral part of the substrate;

a rotating mechanism for rotating the substrate; and

a controlling part,

said film removing member including a plasma supply part ~~provided in a portion facing the predetermined portion~~ for supplying plasma of a reactive gas to the film on the predetermined portion and ~~a two suction port-ports provided facing to each other with said plasma supply part therebetween along a radial direction of the substrate for immediately sucking a plasma supply-supplied from the plasma supply part, said two suction ports being located facing each other along a radial direction of the substrate and said plasma supply part being located between the two suction ports, and~~

said controlling part ~~controlling~~ configured to control a suction pressure of said suction port and flow rate of the plasma ~~supply-supplied~~ from the plasma supply part.

2. - 7. (Canceled)

8. (Original) The processing apparatus as set forth in claim 1, further comprising:

a horizontal driving part for horizontally moving said film removing member.

9. - 10. (Canceled)

11. (Previously Presented) The processing apparatus as set forth in claim 1, wherein

said film removing member is provided at plural positions along a circumferential direction of the substrate.

12. – 16. (Canceled)

17. (Original) The processing apparatus as set forth in claim 1, further comprising:

a removal solution discharge nozzle for discharging a removal solution to the outer peripheral part of the substrate to remove the film on the outer peripheral part, in addition to said film removing member.

18. (Original) The processing apparatus as set forth in claim 1, further comprising:

a coating solution discharge nozzle for discharging a coating solution to the substrate to form the film on the substrate.

19. (Original) The processing apparatus as set forth in claim 1, further comprising:

an oxygen radical supply part for supplying oxygen radicals toward at least an outer peripheral part of a surface, which is different from the surface on which the film is formed, of the substrate.

20. (Original) The processing apparatus as set forth in claim 1, further comprising:

a heating unit for heating the substrate by an infrared ray.

21. (Withdrawn) A processing method for processing a substrate on a surface of which a film is formed, comprising the step of:

forming in the film on an outer peripheral part of the substrate a sloped part such that its film thickness becomes thinner toward an end part.

22. (Withdrawn) The processing method as set forth in claim 21, further comprising the steps of:

selectively removing the film on a portion of the outer peripheral part of the substrate; and
forming the sloped part such that its film thickness becomes thinner toward the portion from which the film is removed.

23. (Withdrawn) The processing method as set forth in claim 21, further comprising the step of:
oxidizing a surface of the sloped part.

24. (Withdrawn) The processing method as set forth in claim 23, wherein the oxidation is performed by supplying oxygen radicals.

25. – 32. (Canceled)